## **Supporting Information**

## Exclusive enhancement of catalytic activity in Bi<sub>0.5</sub>Na<sub>0.5</sub>TiO<sub>3</sub> nanostructures: new insights into the design of efficient piezocatalysts and piezo-photocatalysts

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Figure S1. Raman spectra of two different BNT materials.



Figure S2. SEM image of BNT-2.



Figure S3. Size distribution histograms of (a) BNT-1 and (b) BNT-2. (c)  $N_2$  adsorptiondesorption isotherms of BNT-1 and BNT-2 (inset shows the calculated BET surface area and pore volume).



Figure S4. (a) The  $H_2$  production, (b) Cr(VI) reduction and (c) RhB degradation curves with BNT-2 under different conditions.



**Figure S5.** Active-species-trapping experiments for RhB degradation using BNT-1 under (a) light illumination and (b) simultaneous ultrasonic vibration and irradiation by simulated sunlight.



**Figure S6.** FEM simulation for the piezoelectric potential distribution in (a) BNT-1 and (b) BNT-2 under cavitation pressure of 0.1 MPa, respectively.



Figure S7. Electronic band structure of bulk BNT at the space group R3c. The horizontal solid line indicates the position of the Fermi level.

The first-principles calculations were performed in the framework of density functional theory (DFT). The electronic band gap of the studied materials was obtained via running the Vienna *ab initio* simulation package. The core-valence interactions were treated by the projector augmented wave (PAW) method, where the plane wave expansion was truncated with a cutoff energy of 500 eV. We employed the exchange-correlation functional as the generalized gradient approximation (GGA) in the Perdew-Burke-Ernzerhof (PBE) formalism. To better determine the value of band gap, a two dimensional dense k-mesh with a 20  $\times$  20 Monkhorst-Pack grid in momentum space was used in self-consistent calculations.

Catalysts	Catalytic	Catalytic	<b>First-order</b>	Ref.
	conditions	applications	rate constant	
BNT	Ultrasonic (40 kHz, 110	Degradation of RhB	0.0343 min <sup>-1</sup>	This
(nanosphere, ~100 nm)	W), room temperature	$(10 \text{ mg } \text{L}^{-1})$		work
BaTiO <sub>3</sub> (nanorod	Ultrasonic (40 kHz, 200	Degradation of RhB	0.0044 min <sup>-1</sup>	[72]
and nanoparticle, ~100-200 nm)	W), room temperature	$(10 \text{ mg } \text{L}^{-1})$		
ZnO	Ultrasonic (40 kHz, 200	Degradation of RhB	0.0087 min <sup>-1</sup>	[72]
(nanoparticle, ~20-30 nm)	W), room temperature	$(10 \text{ mg } L^{-1})$		
NaNbO <sub>3</sub> (nanowire, ~200 nm in width and ~4 µm in length)	Ultrasonic (40 kHz, 120 W), room temperature	Degradation of RhB (10 mg L <sup>-1</sup> )	0.0161 min <sup>-1</sup>	[73]

 Table S1. Experimental conditions and first-order rate constants of reported

 piezoelectric materials.

**Table S2.** The measured electrical conductivity of BNT-1 based bulk sample at room temperature.

	Resistivity	Conductivity	
Serial number	(Ωm)	(S/m)	
1	72700	1.376E-05	
2	72300	1.383E-05	
3	72300	1.383E-05	
4	72700	1.376E-05	
5	72300	1.383E-05	

Table S3. Band gap	energy variation	of BNT u	nder different	mechanical	force l	based
on DFT calculations.						

0 MPa	1 MPa	100 MPa	500 MPa
2.751 eV	2.747 eV	2.745 eV	2.732 eV